Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel Dual Gate MOS Type

3SK226

TV Tuner, VHF RF Amplifier Applications FM Tuner Applications

- Superior cross modulation performance.
- Low reverse transfer capacitance: $C_{rss} = 0.015 \text{ pF (typ.)}$
- Low noise figure: NF = 1.1dB (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	13.5	V
Gate 1-source voltage	V_{G1S}	±8	V
Gate 2-source voltage	V_{G2S}	±8	V
Drain current	I _D	30	mA
Drain power dissipation	P_{D}	150	mW
Channel temperature	T _{ch}	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

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2. GATE 2
3. DRAIN
SMQ 4. SOURCE

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JETA

TOSHIBA

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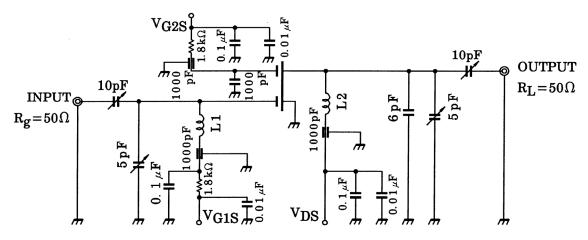
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Weight: 0.013 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate 1 leakage current	I _{G1SS}	$V_{DS} = 0$, $V_{G1S} = \pm 6$ V, $V_{G2S} = 0$	_	_	±50	nA
Gate 2 leakage current	I _{G2SS}	$V_{DS} = 0, V_{G1S} = 0, V_{G2S} = \pm 6 V$	_	_	±50	nA
Drain-source voltage	V (BR) DSX	$V_{G1S} = -4 \text{ V}, V_{G2S} = -4 \text{ V}, I_D = 100 \mu\text{A}$	13.5	_		V
Drain current	I _{DSS}	$V_{DS} = 6 \text{ V}, V_{G1S} = 0, V_{G2S} = 4.5 \text{ V}$	0	_	0.1	mA
Gate 1-source cut-off voltage	V _{G1S} (OFF)	$V_{DS} = 6 \text{ V}, V_{G2S} = 4.5 \text{ V}, I_D = 100 \mu\text{A}$	0	_	1.0	V
Gate 2-source cut-off voltage	V _{G2S} (OFF)	$V_{DS} = 6 \text{ V}, V_{G1S} = 4 \text{ V}, I_D = 100 \mu A$	0.5	1.0	1.5	V
Forward transfer admittance	Y _{fs}	$V_{DS} = 6 \text{ V}, V_{G2S} = 4.5 \text{ V}, I_D = 10 \text{ mA},$ f = 1 kHz	_	13	_	mS
Input capacitance	C _{iss}	V _{DS} = 6 V, V _{G2S} = 4.5 V, I _D = 10 mA,	2.1	2.7	3.3	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	0.015	0.03	pF
Power gain	G _{ps}	V _{DS} = 6 V, V _{G2S} = 4.5 V, I _D = 10 mA,	23	27	_	dB
Noise figure	NF	f = 200 MHz (Figure 1)	_	1.1	2.2	dB



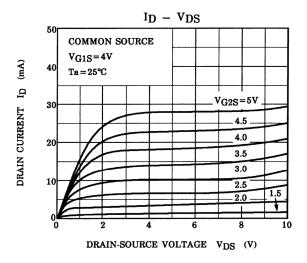
L1: 1 mm ϕ Ag plated copper wire, 2 turns, 8 mm ID

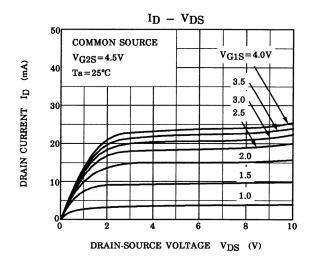
L2: 1 mm Ag plated copper wire, 2.5 turns, 8 mm ID

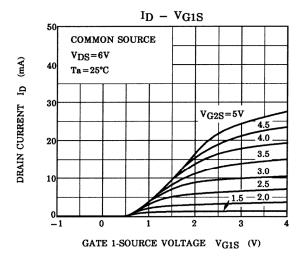
Figure 1 200 MHz, G_{ps} NF Test Circuit

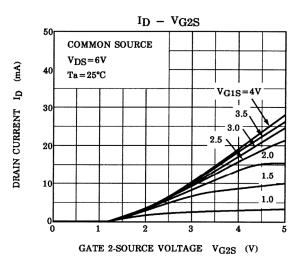
Marking

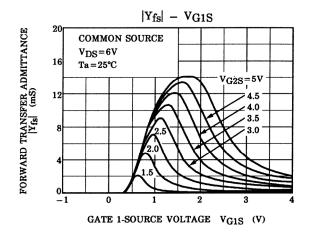


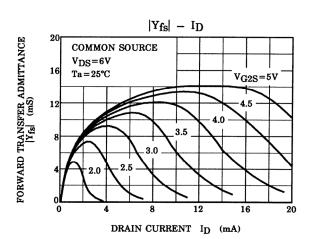




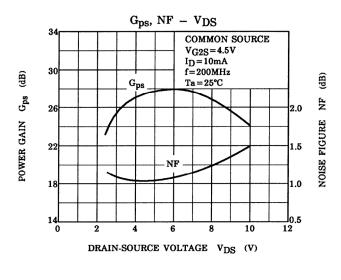


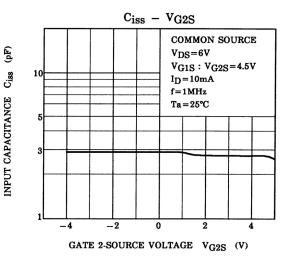


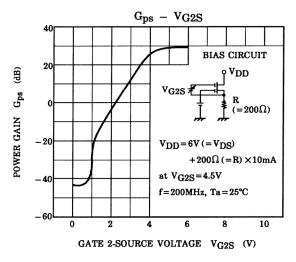


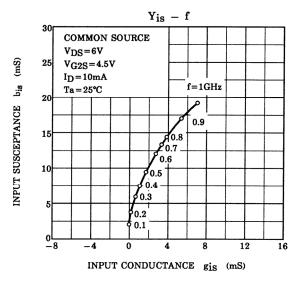


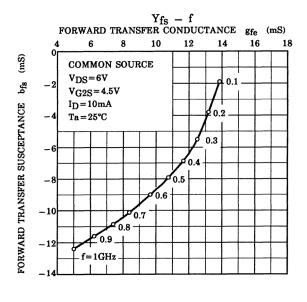
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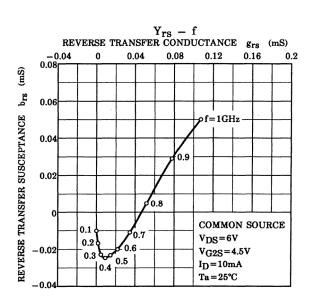


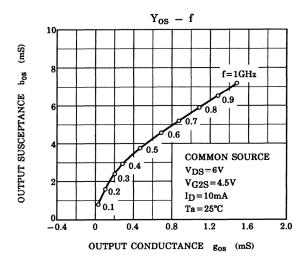


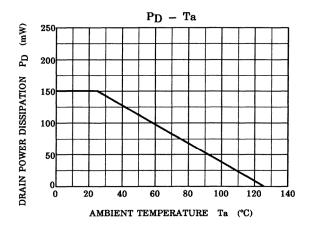












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20070701-EN GENERAL

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